

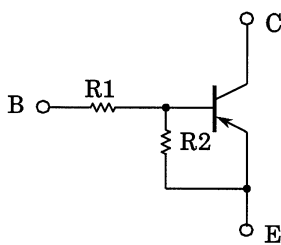
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

RN2101, RN2102, RN2103, RN2104, RN2105, RN2106

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

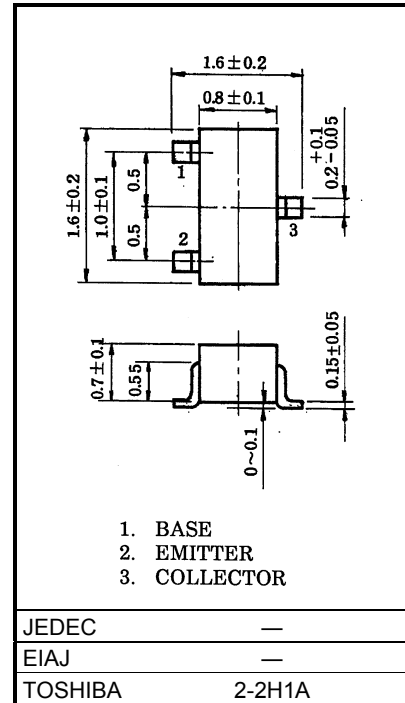
- Built-in bias resistors
- Simplified circuit design
- Fewer parts and simplified manufacturing process
- Complementary to RN1101~RN1106

Equivalent Circuit and Bias Resistor Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2101	4.7	4.7
RN2102	10	10
RN2103	22	22
RN2104	47	47
RN2105	2.2	47
RN2106	4.7	47

Unit: mm



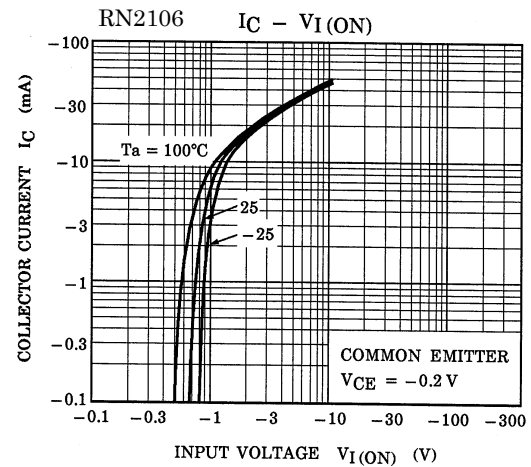
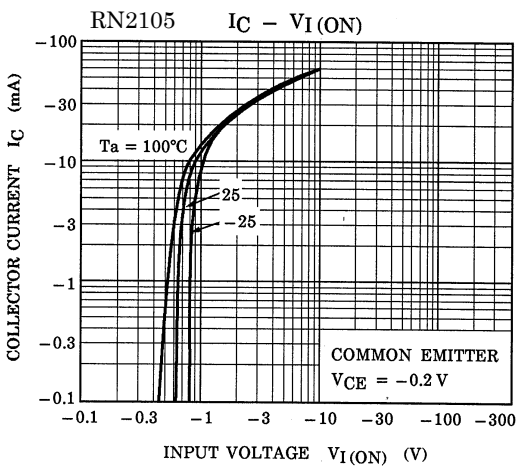
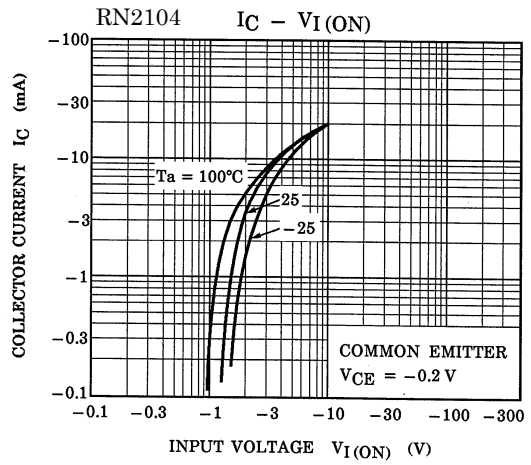
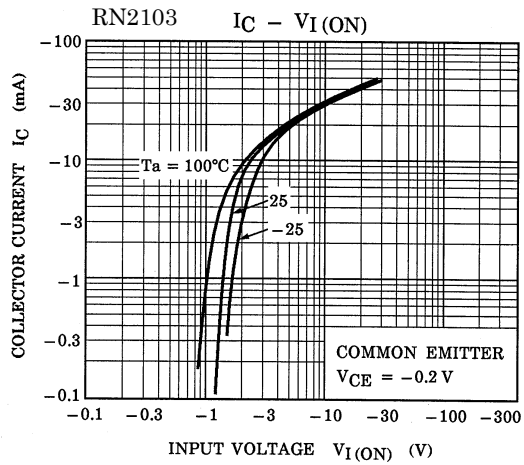
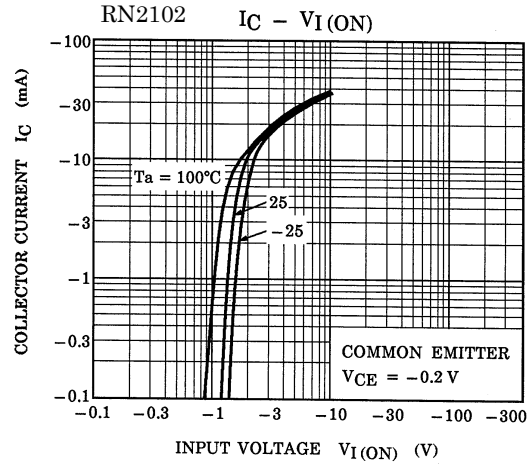
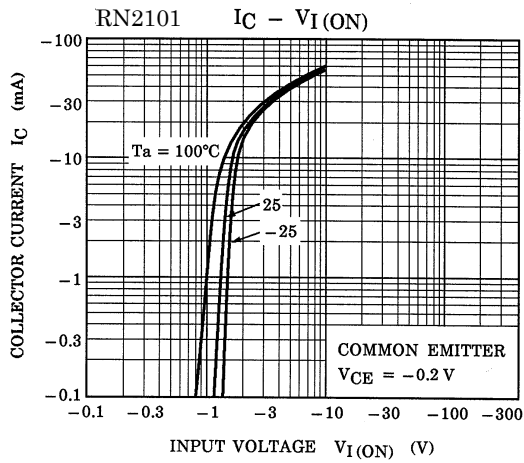
Weight: 2.4 mg

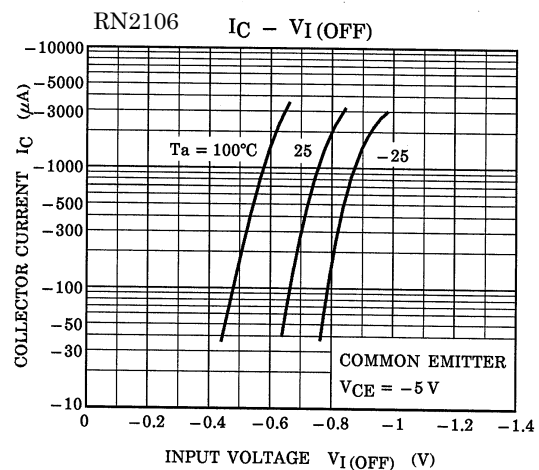
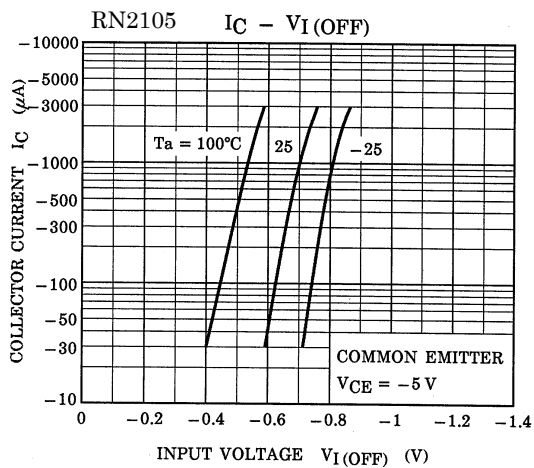
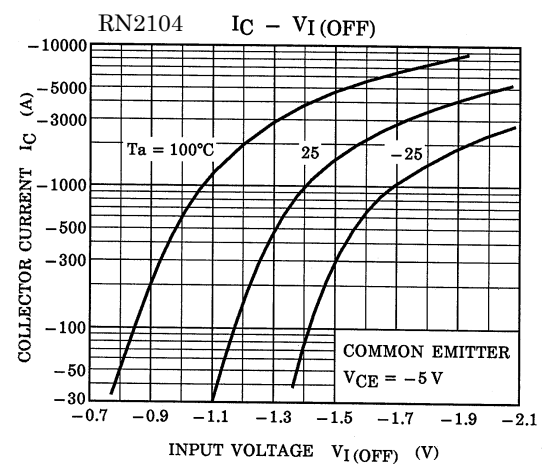
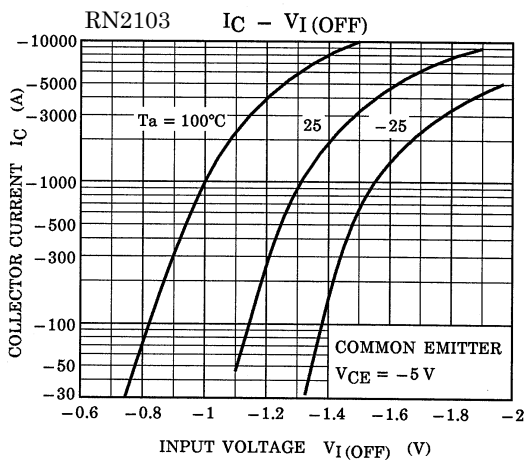
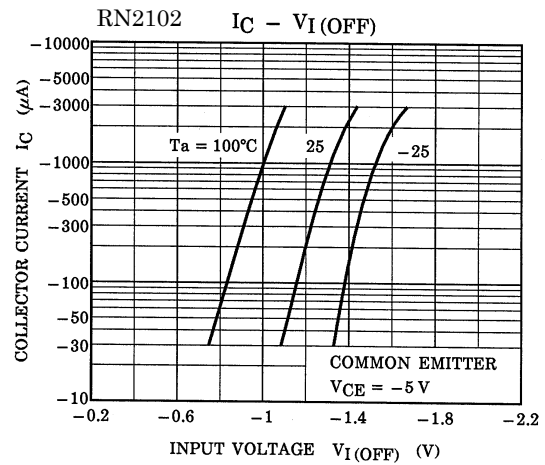
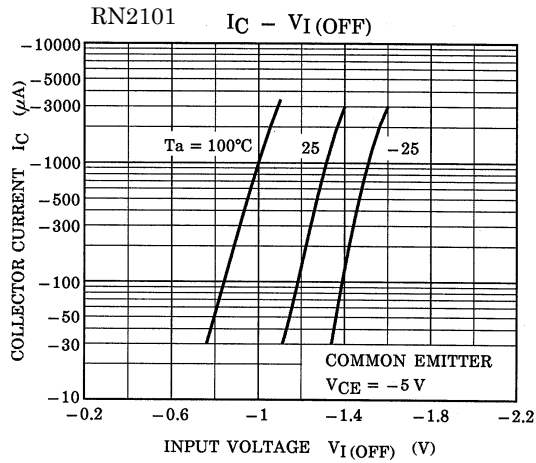
Maximum Ratings (Ta = 25°C)

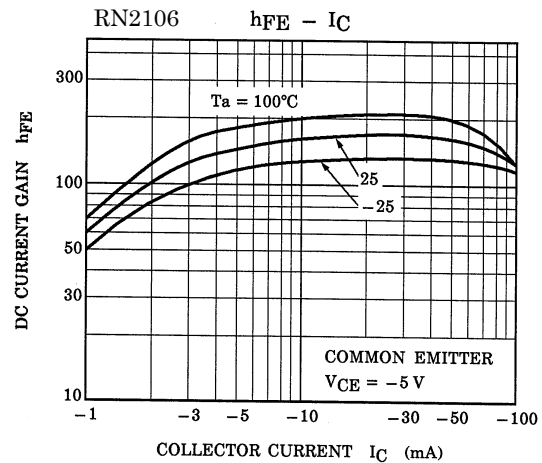
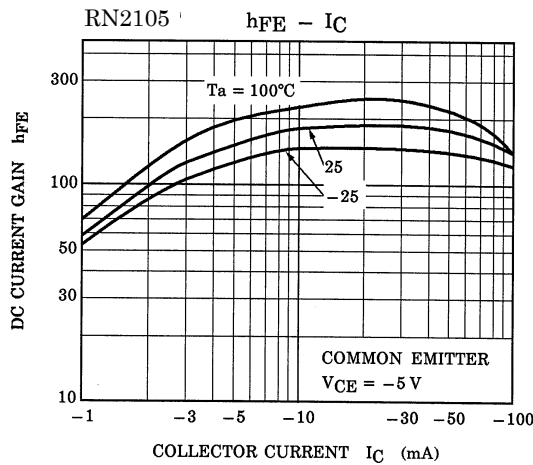
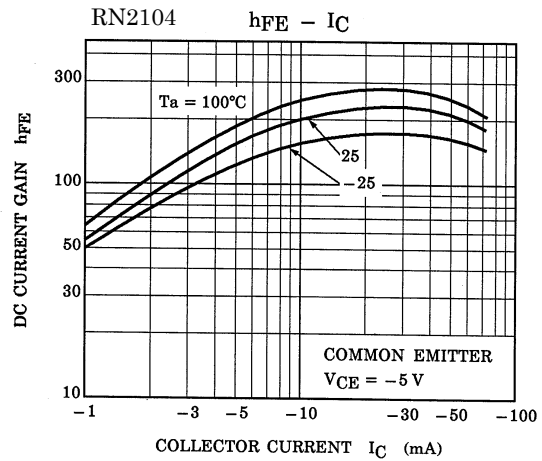
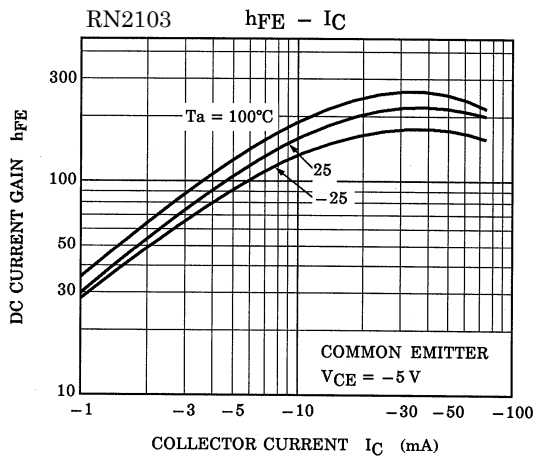
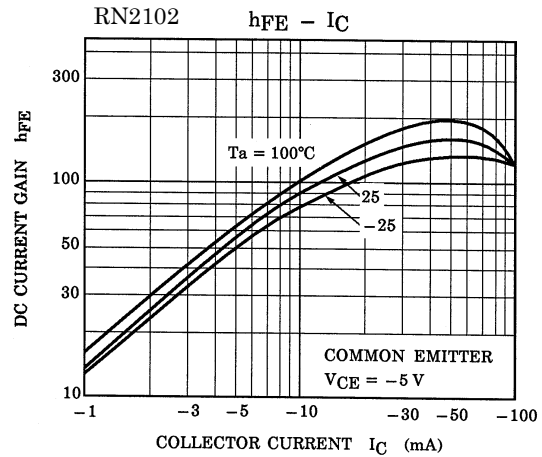
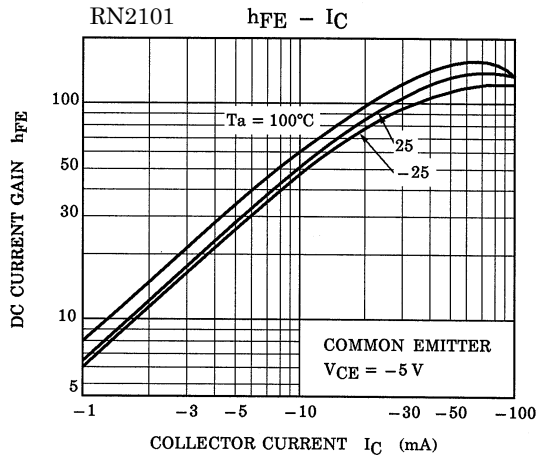
Characteristic	Symbol	Rating	Unit	
Collector-base voltage	RN2101~2106	V _{CBO}	-50	V
Collector-emitter voltage		V _{CEO}	-50	V
Emitter-base voltage	RN2101~2104	V _{EBO}	-10	V
	RN2105, 2106		-5	
Collector current	RN2101~2106	I _C	-100	mA
Collector power dissipation		P _C	100	mW
Junction temperature		T _j	150	°C
Storage temperature range		T _{stg}	-55~150	°C

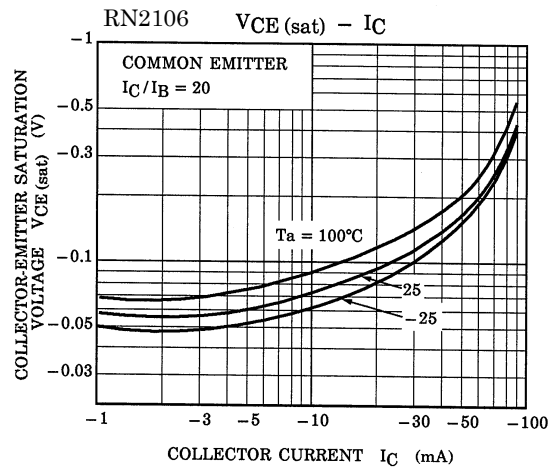
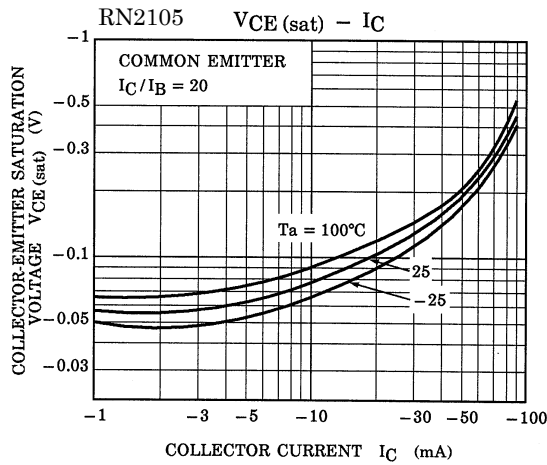
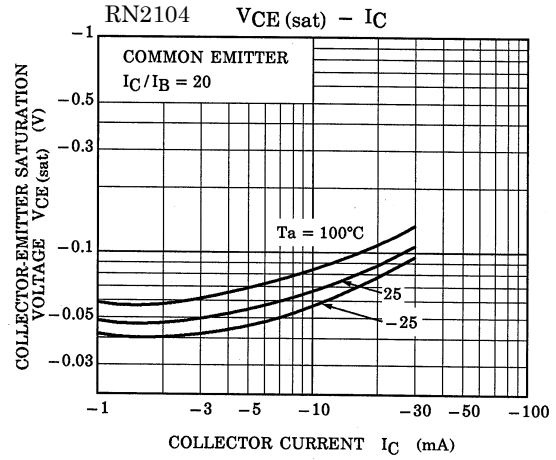
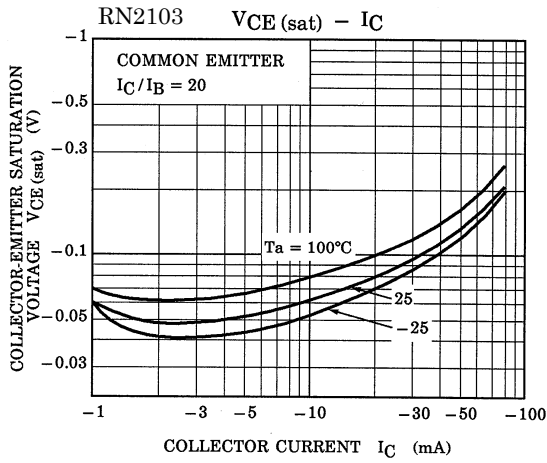
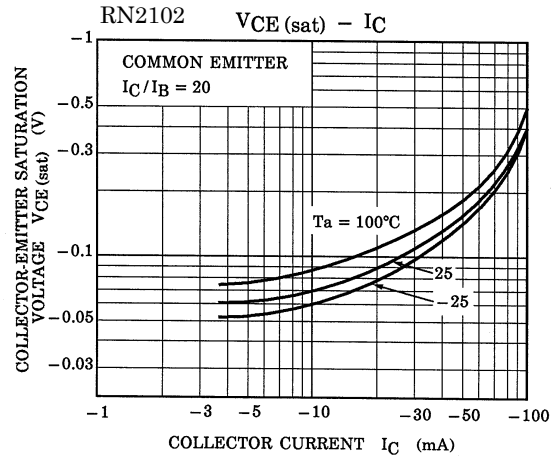
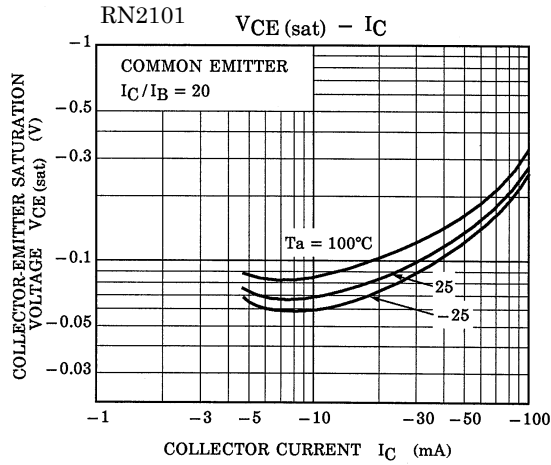
Electrical Characteristics (Ta = 25°C)

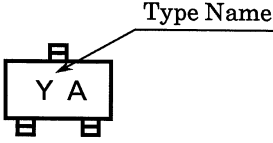
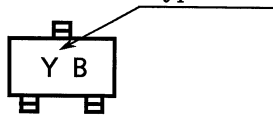
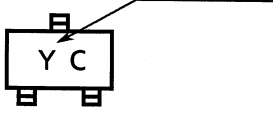
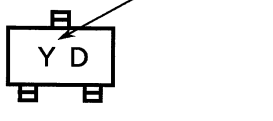
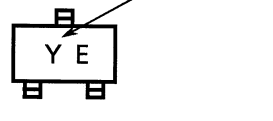
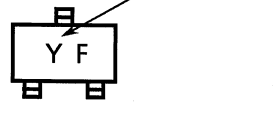
Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN2101~2106	I_{CBO}	—	$V_{CB} = -50\text{ V}, I_E = 0$	—	—	-100	nA
		I_{CEO}	—	$V_{CE} = -50\text{ V}, I_B = 0$	—	—	-500	
Emitter cut-off current	RN2101	I_{EBO}	—	$V_{EB} = -10\text{ V}, I_C = 0$	-0.82	—	-1.52	mA
	RN2102				-0.38	—	-0.71	
	RN2103				-0.17	—	-0.33	
	RN2104				-0.082	—	-0.15	
	RN2105			$V_{EB} = -5\text{ V}, I_C = 0$	-0.078	—	-0.145	
	RN2106				-0.074	—	-0.138	
DC current gain	RN2101	h_{FE}	—	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	30	—	—	
	RN2102				50	—	—	
	RN2103				70	—	—	
	RN2104				80	—	—	
	RN2105				80	—	—	
	RN2106				80	—	—	
Collector-emitter saturation voltage	RN2101~2106	$V_{CE(sat)}$	—	$I_C = -5\text{ mA}, I_B = -0.25\text{ mA}$	—	-0.1	-0.3	V
Input voltage (ON)	RN2101	$V_{I(ON)}$	—	$V_{CE} = -0.2\text{ V}, I_C = -5\text{ mA}$	-1.1	—	-2.0	V
	RN2102				-1.2	—	-2.4	
	RN2103				-1.3	—	-3.0	
	RN2104				-1.5	—	-5.0	
	RN2105				-0.6	—	-1.1	
	RN2106				-0.7	—	-1.3	
Input voltage (OFF)	RN2101~2104	$V_{I(OFF)}$	—	$V_{CE} = -5\text{ V}, I_C = -0.1\text{ mA}$	-1.0	—	-1.5	V
	RN2105, 2106				-0.5	—	-0.8	
Transition frequency	RN2101~2106	f_T	—	$V_{CE} = -10\text{ V}, I_C = -5\text{ mA}$	—	200	—	MHz
Collector Output capacitance	RN2101~2106	C_{ob}	—	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	3	6	pF
Input resistor	RN2101	R1	—		3.29	4.7	6.11	kΩ
	RN2102				7	10	13	
	RN2103				15.4	22	28.6	
	RN2104				32.9	47	61.1	
	RN2105				1.54	2.2	2.86	
	RN2106				3.29	4.7	6.11	
Resistor ratio	RN2101~2104	R1/R2	—		0.9	1.0	1.1	
	RN2105				0.0421	0.0468	0.0515	
	RN2106				0.09	0.1	0.11	









Type Name	Marking
RN2001	
RN2102	
RN2103	
RN2104	
RN2105	
RN2106	

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060116EAA

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